SK 100 TAA



SEMITOP[®]2

Two separated thyristors

SK 100 TAA

Target Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chips
- Up to 1600 reverse voltage
- High surge currents

Typical Applications

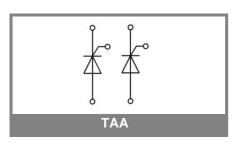
- Brake chopper
- Soft starters

V _{RSM}	V _{RRM} , V _{DRM}	I _T = 100 A
V	V	(T _s = 80 °C)
900	800	SK 100 TAA 08
1300	1200	SK 100 TAA 12
1700	1600	SK 100 TAA 16

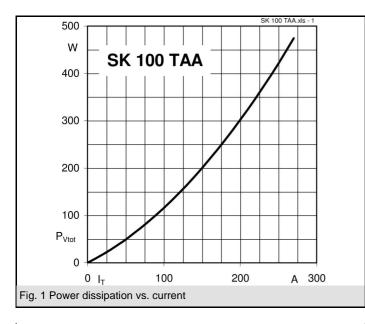
Ts = 25°C unless otherwise specified

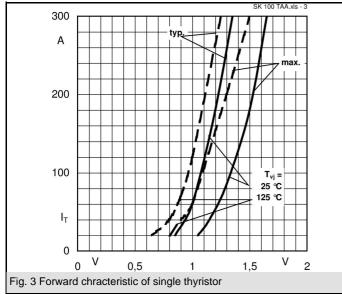
Characteristics

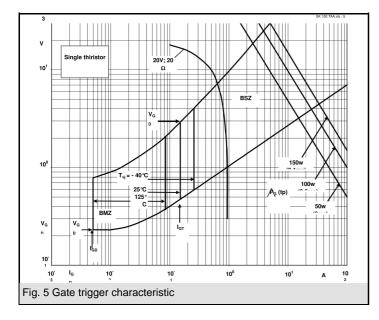
Symbol	Conditions	Values	Unit
T	Ts = 100°C	65	А
I _T	Ts = 80°C	100	А
			А
I _{TSM} /I _{FSM}	T _{vi} = 25 (125) °C; 10 ms	2000 (1800)	Α
l²t	T _{vj} = 25 (125) °C; half sine wave, 10 ms	20000 (16200)	A²s
T _{stg}		-40 + 125	°C
T _{solder}	terminals, 10 s	260	°C
Thyristo	r	1	
(dv/dt) _{cr}	T _{vi} = 125 °C	1000	V/µs
di/dt) _{cr}	T _{vi} = 125 °C; f = 50 60 Hz	50	A/µs
q	T _{vi} = 125 °C; typ.	80	μs
ч Н	T _{vi} = 25 °C; typ. / max.	100 / 200	mA
L	$T_{vi}^{,j}$ = 25 °C; R _G = 33 Ω; typ. / max.	200 / 500	mA
/ _T	$T_{vi} = 25 \text{ °C}; (I_T = 300 \text{ A}); \text{ max.}$	1,85	V
/ _{T(TO)}	$T_{vi}^{0} = 125 \text{ °C}$	max. 0,9	V
т	T _{vi} = 125 °C	max. 3,5	mΩ
, _{DD} ; I _{RD}	T_{vj}^{vj} = 125 °C; V_{DD} = V_{DRM} ; V_{RD} = V_{RRM}	max. 20	mA
R _{th(j-s)}	cont. per thyristor	0,45	K/W
Г _{vj}		-40 +125	°C
√ _{GT}	T _{vi} = 25 °C; d.c.	2	V
GT	$T_{vi}^{vj} = 25 ^{\circ}C; d.c.$	100	mA
V _{GD}	T_{vi}^{vj} = 125 °C; d.c.	0,25	V
GD	T _{vi} = 125 °C; d.c.	5	mA
Diode			
/ _F	$T_{vi} = ^{\circ}C; (I_F = A); max.$		V
/ _(TO)	$T_{vi}^{ij} = °C$		V
Т	$T_{vi}^{ij} = °C$		mΩ
RD	$T_{vi} = °C; V_{RD} = V_{RRM}$		mA
R _{th(j-s)}			K/W
Г _{vi}			°C
	cal data	1	
V _{isol}	AC 50Hz, r.m.s. 1min (1sec)	2500 (3000)	V
M ₁	mounting torque	2	Nm
w		19	g
Case	SEMITOP [®] 2	T 81	

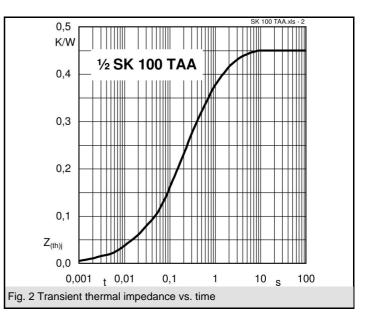


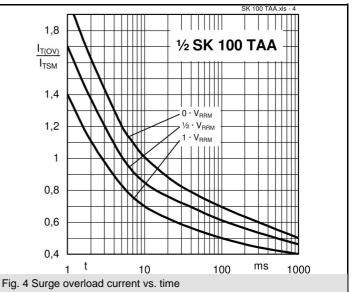
SK 100 TAA



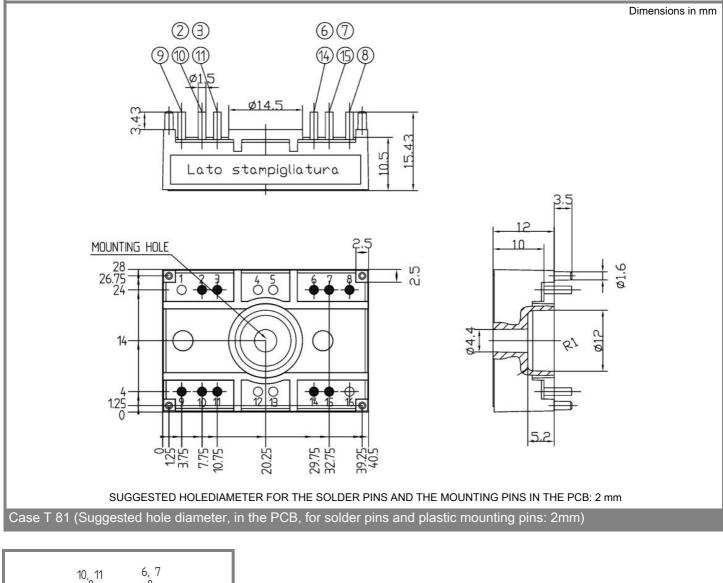


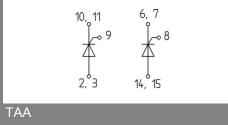






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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